

S/N 10/028,643

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

Applicant: Kie Y. Ahn et al.

Examiner: Long Pham

Serial No.: 10/028,643

Group Art Unit: 2823

Filed: December 20, 2001

Docket: 1303030US1

Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN GATE DIELECTRICS

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
Washington, D.C. 20231

In response to the Restriction Requirement mailed August 21, 2002, Applicant elects, without traverse, claims 1-12 and 55 drawn to a method of making a field effect transistor. Applicant affirms that, as noted by the examiner, claim 1 is generic to the second species (claims 22-29) and the third species (claims 30-37).

The Examiner is invited to contact Applicant's Representatives at the below-listed telephone number if there are any questions regarding this Response or if prosecution of this application may be assisted thereby.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 9-12-02

By [Signature]

David C. Peterson
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, Washington, D.C. 20231, on this 12th day of September, 2002.

Name

Amy Moriarty

Signature

[Signature]